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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HZM6.2ZMWA

Silicon Epitaxial Planar Zener Diode for Surge Absorb



ADE-208-1514 (Z)

Rev.0
May. 2002

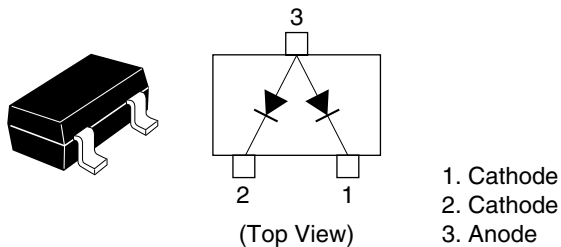
Features

- HZM6.2ZMWA has two devices in a monolithic, and can absorb surge.
- Low capacitance ($C = 8.5 \text{ pF max}$) and can protect ESD of signal line.
- MPAK Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HZM6.2ZMWA	62N	MPAK

Pin Arrangement



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd *	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: Two device total, See Fig.2.

Electrical Characteristics*¹

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Zener voltage	V _z	5.90	—	6.50	V	I _z = 5 mA, 40 ms pulse
Reverse current	I _R	—	—	3	μA	V _R = 5.5 V
Capacitance	C	—	—	8.5	pF	V _R = 0 V, f = 1 MHz
Dynamic resistance	r _d	—	—	60	Ω	I _z = 5 mA
ESD-Capability * ²	—	13	—	—	kV	C = 150 pF, R = 330 Ω, Both forward and reverse direction 10 pulse

Notes: 1. Per one device.

2. Failure criterion ; I_R > 3 μA at V_R = 5.5 V.

Main Characteristics

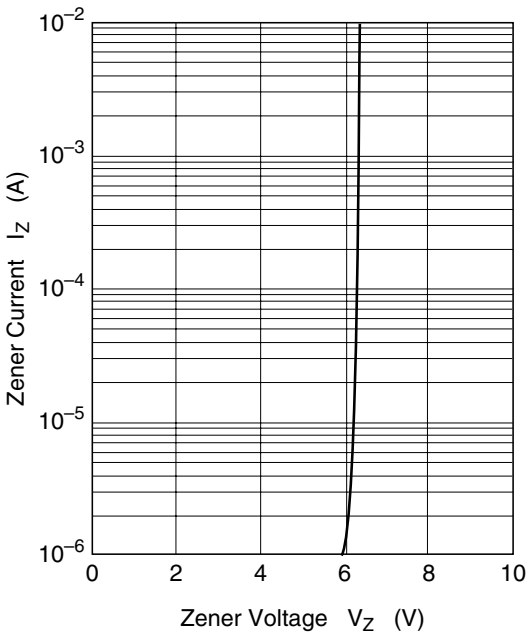


Fig.1 Zener current vs. Zener voltage

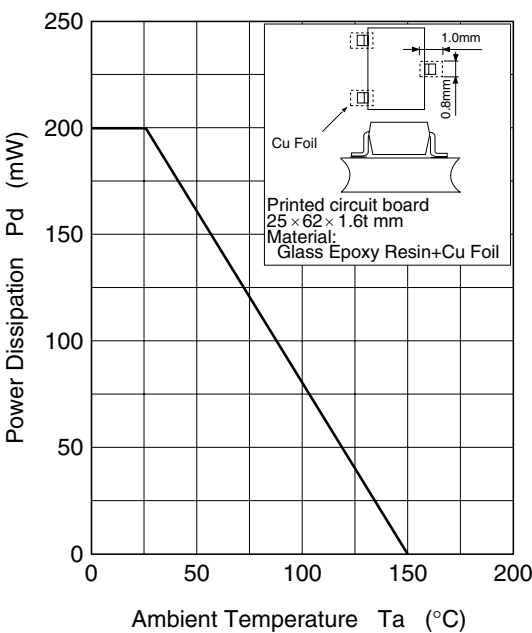


Fig.2 Power Dissipation vs. Ambient Temperature

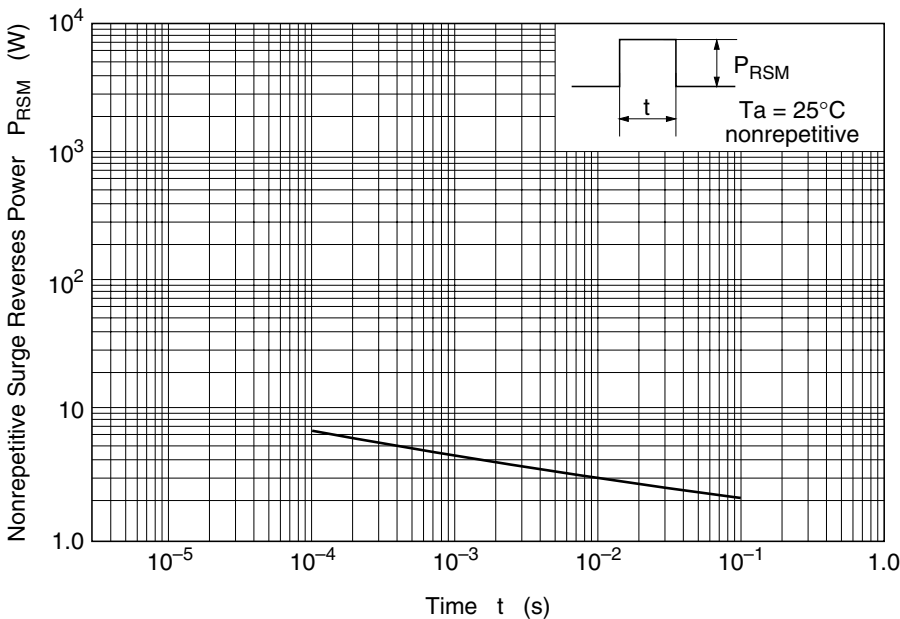


Fig.3 Surge Reverse Power Ratings

Main Characteristics (cont)

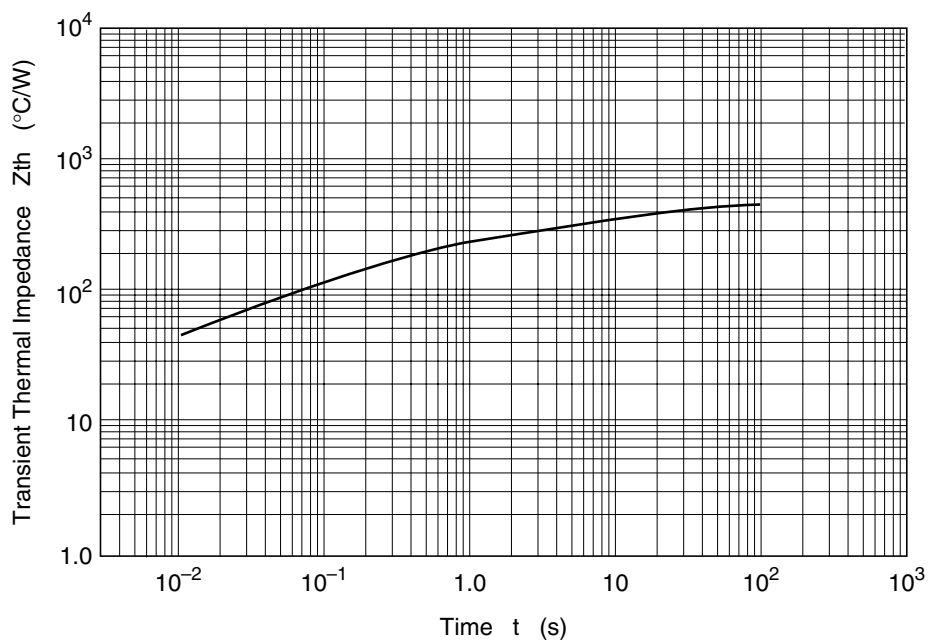


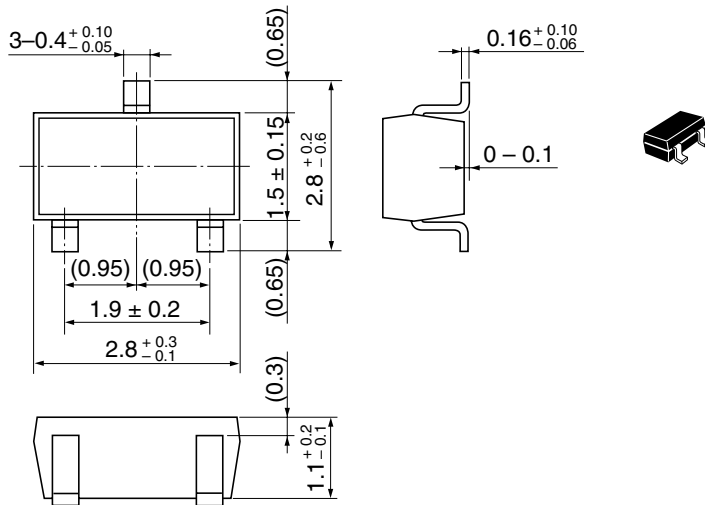
Fig.4 Transient Thermal Impedance *

Note: Measurement value by forward bias.

Package Dimensions

As of January, 2002

Unit: mm



Hitachi Code	MPAK
JEDEC	—
JEITA	Conforms
Mass (reference value)	0.011 g

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